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(54) Title: PROCESS FOR MANUFACTURE OF SEMICONDUCTOR DEVICES

(57) Abstract: A process for the manufacture of semiconductor devices is provided. The process comprises the chemical-mechanical polishing of a substrate or layer containing at least one III-V material in the presence of a chemical-mechanical polishing composition (Q1) comprising (A) inorganic particles, organic particles, or a mixture or composite thereof, (B) a polymer comprising at least one N-heterocycle, and (M) an aqueous medium and whereas Q1 has a pH of from 1.5 to 4.5.